

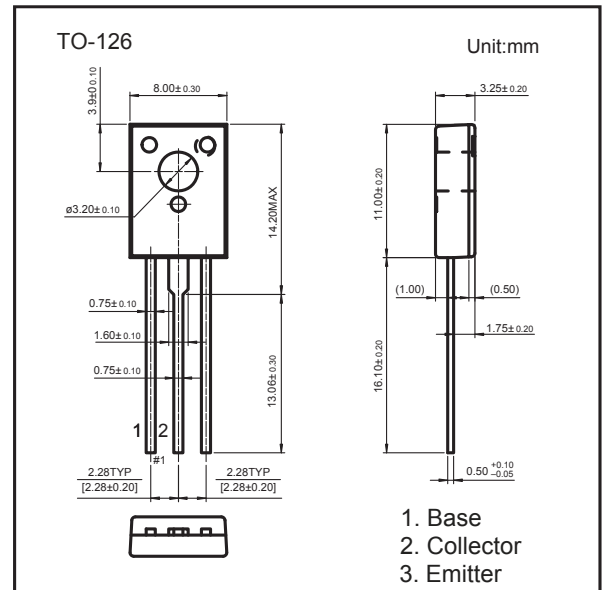
## TO-126 Plastic-Encapsulate Transistors

### FEATURES

- PNP TRANSISTORS
- Collector-Base Voltage:  $V_{CB0}=-60V$

### MECHANICAL DATA

- Case style:TO-126 molded plastic
- Mounting position:any



## MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CB0}$	Collector-Base Voltage	-40	V
$V_{CE0}$	Collector-Emitter Voltage	-30	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current -Continuous	-3	A
$P_C$	Collector Power Dissipation	1.25	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	100	°C/W
$T_j$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature	-55-150	°C

### PACKAGE INFORMATION

Device	Package	Shipping
B772	TO-126	500/Tape&Reel

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_C=-100\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CE0}$	$I_C=-10mA, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-6			V
Collector cut-off current	$I_{CB0}$	$V_{CB}=-40V, I_E=0$			-1	$\mu A$
Collector cut-off current	$I_{CE0}$	$V_{CE}=-30V, I_B=0$			-10	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-6V, I_C=0$			-1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=-2V, I_C=-1A$	60		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-0.2A$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-2A, I_B=-0.2A$			-1.5	V
Transition frequency	$f_T$	$V_{CE}=-5V, I_C=-0.1A$ $f=10MHz$	50	80		MHz

### CLASSIFICATION OF $h_{FE}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

## Typical Characteristics

